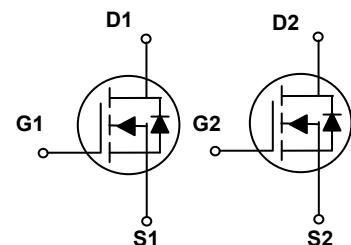
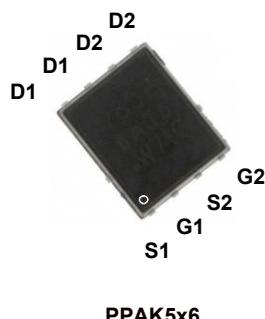


Main Product Characteristics

BV _{DSS}	100V
R _{DS(ON)}	24mΩ
I _D	25A



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFP1026 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous ($T_C=25^\circ\text{C}$)	I _D	25	A
Drain Current-Continuous ($T_C=100^\circ\text{C}$)		15.8	A
Drain Current-Pulsed ¹	I _{DM}	100	A
Single Pulse Avalanche Energy ²	E _{AS}	51	mJ
Single Pulse Avalanche Current ²	I _{AS}	32	A
Power Dissipation ($T_C=25^\circ\text{C}$)	P _D	50	W
Power Dissipation-Derate Above 25°C		0.4	W/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62	°C/W
Thermal Resistance, Junction-to-Case	R _{θJC}	2.48	°C/W
Storage Temperature Range	T _{STG}	-55 To +150	°C
Operating Junction Temperature Range	T _J	-55 To +150	°C

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	100	-	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=80\text{V}, V_{\text{GS}}=0\text{V}, T_J=25^\circ\text{C}$	-	-	1	μA
		$V_{\text{DS}}=80\text{V}, V_{\text{GS}}=0\text{V}, T_J=85^\circ\text{C}$	-	-	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
On Characteristics						
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=14\text{A}$	-	20	24	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=10\text{A}$	-	27	35	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1.2	1.6	2.5	V
Forward Transconductance	g_{fs}	$V_{\text{DS}}=10\text{V}, I_{\text{D}}=3\text{A}$	-	9	-	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{3,4}	Q_g	$V_{\text{DS}}=50\text{V}, I_{\text{D}}=10\text{A}, V_{\text{GS}}=15\text{V}$	-	12.5	20	nC
Gate-Source Charge ^{3,4}	Q_{gs}		-	1.5	3	
Gate-Drain Charge ^{3,4}	Q_{gd}		-	4.3	6	
Turn-On Delay Time ^{3,4}	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=50\text{V}, R_{\text{G}}=6\Omega$ $V_{\text{GS}}=10\text{V}, I_{\text{D}}=15\text{A}$	-	20	30	nS
Rise Time ^{3,4}	t_r		-	30	45	
Turn-Off Delay Time ^{3,4}	$t_{\text{d}(\text{off})}$		-	55	70	
Fall Time ^{3,4}	t_f		-	30	45	
Input Capacitance	C_{iss}	$V_{\text{DS}}=50\text{V}, V_{\text{GS}}=0\text{V}, F=1\text{MHz}$	-	690	1030	pF
Output Capacitance	C_{oss}		-	135	220	
Reverse Transfer Capacitance	C_{rss}		-	6	15	
Gate Resistance	R_g	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=0\text{V}, F=1\text{MHz}$	-	0.8	-	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_s	$V_G=V_D=0\text{V}, \text{Force Current}$	-	-	25	A
Pulsed Source Current	I_{SM}		-	-	50	A
Diode Forward Voltage	V_{SD}	$V_{\text{GS}}=0\text{V}, I_s=1\text{A}, T_J=25^\circ\text{C}$	-	-	1	V
Reverse Recovery Time	T_{rr}	$V_R=100\text{V}, I_s=10\text{A}, \text{di}/\text{dt}=100\text{A}/\mu\text{s}, T_J=25^\circ\text{C}$	-	180	-	nS
Reverse Recovery Charge	Q_{rr}		-	300	-	nC

Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2. $V_{\text{DD}}=50\text{V}, L=0.1\text{mH}, I_{\text{AS}}=32\text{A}, R_{\text{G}}=25\Omega$, starting $T_J=25^\circ\text{C}$.
3. Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
4. Essentially independent of operation temperature.

Typical Electrical and Thermal Characteristic Curves

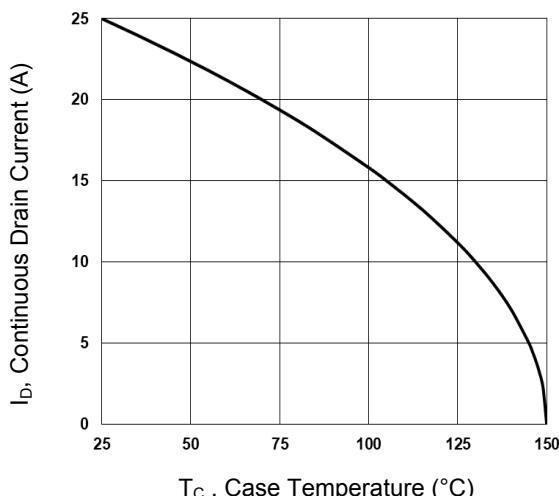


Fig.1 Continuous Drain Current vs. T_c

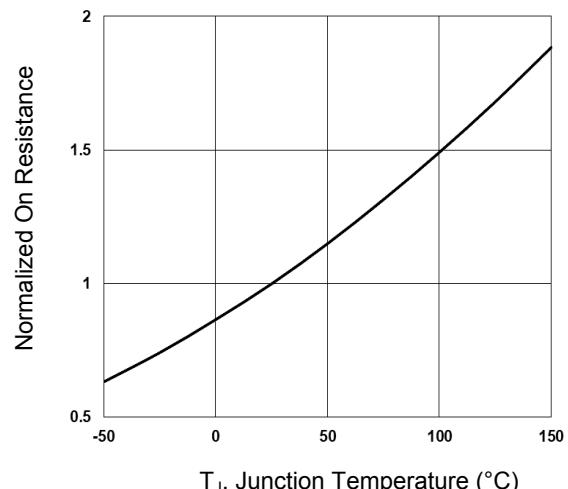


Fig.2 Normalized $R_{DS(ON)}$ vs. T_j

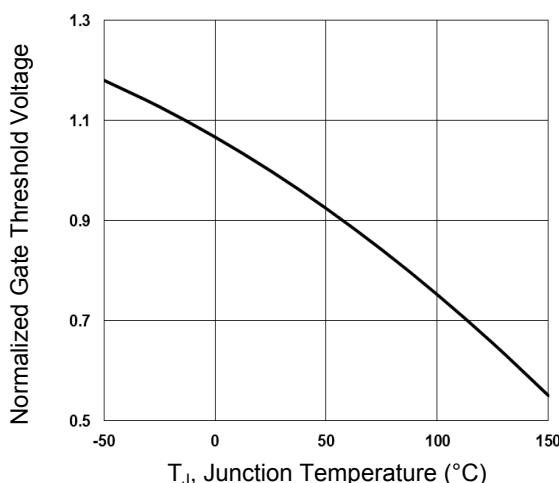


Fig.3 Normalized V_{th} vs. T_j

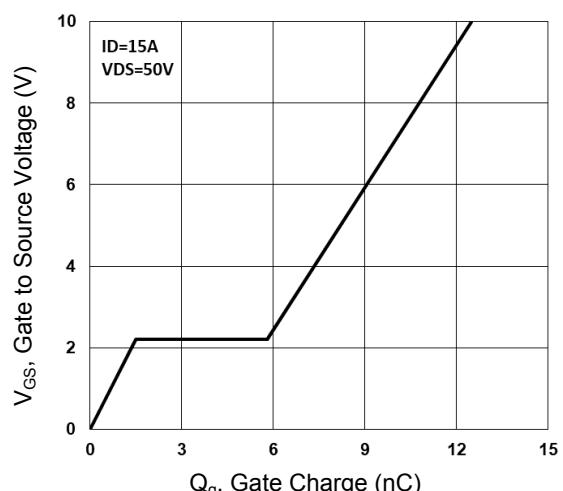


Fig.4 Gate Charge Characteristics

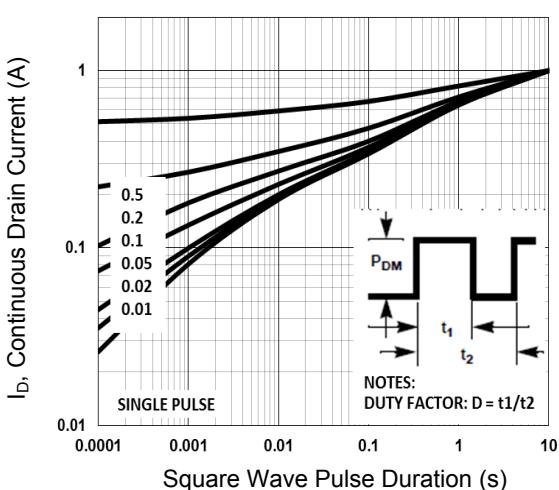


Fig.5 Normalized Transient Impedance

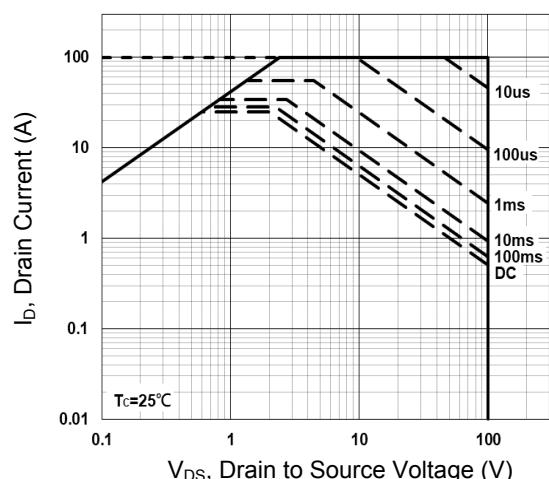


Fig.6 Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

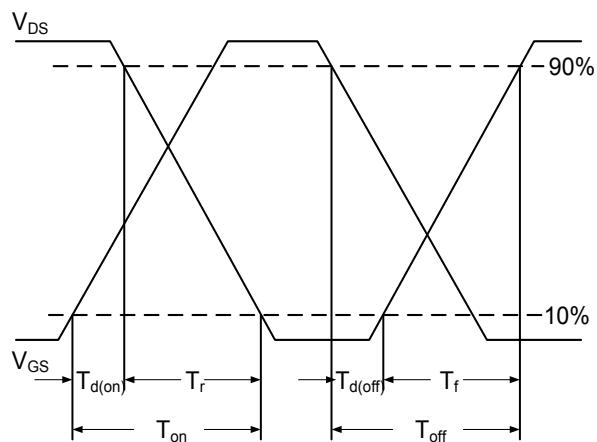


Fig.7 Switching Time Waveform

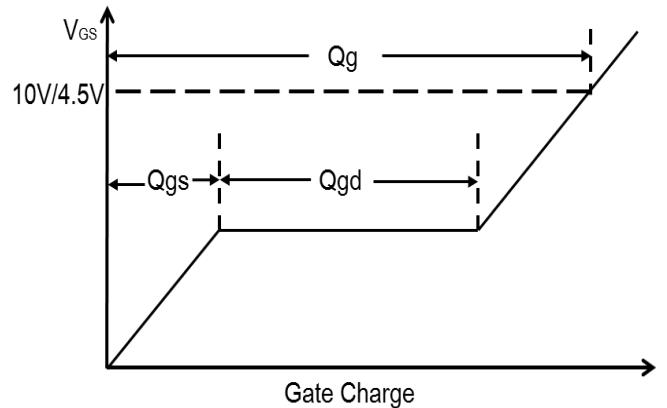
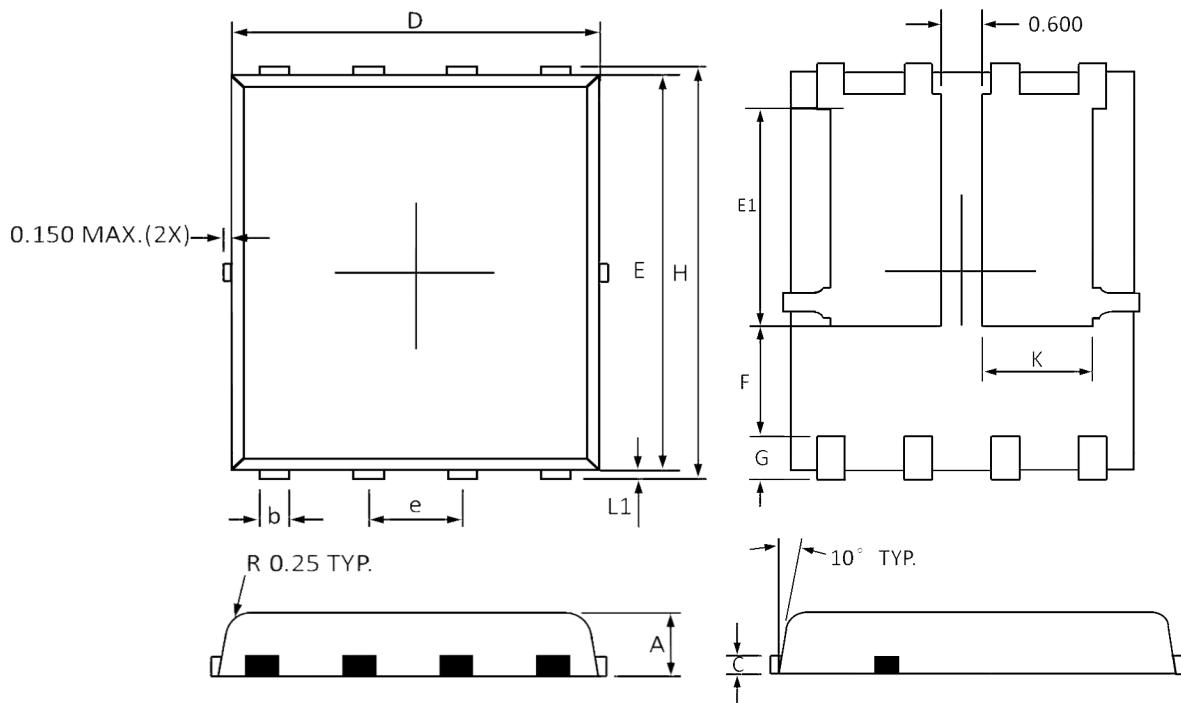


Fig.8 Gate Charge Waveform

Package Outline Dimensions

PPAK5x6



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.800	1.200	0.031	0.047
b	0.300	0.510	0.012	0.020
C	0.250 Ref		0.010 Ref	
D	4.800	5.400	0.189	0.213
E	5.450	5.960	0.215	0.235
E1	3.200	3.800	0.126	0.150
e	1.27 BSC		0.050 BSC	
F	1.000	1.900	0.039	0.075
G	0.380	0.800	0.015	0.031
H	5.850	6.300	0.230	0.248
L1	0.050	0.250	0.002	0.010
K	1.500	1.900	0.059	0.074

Recommended Pad Layout

